

EL303  
ANALOG INTEGRATED CIRCUITS LAB #2  
Folded Cascode Design

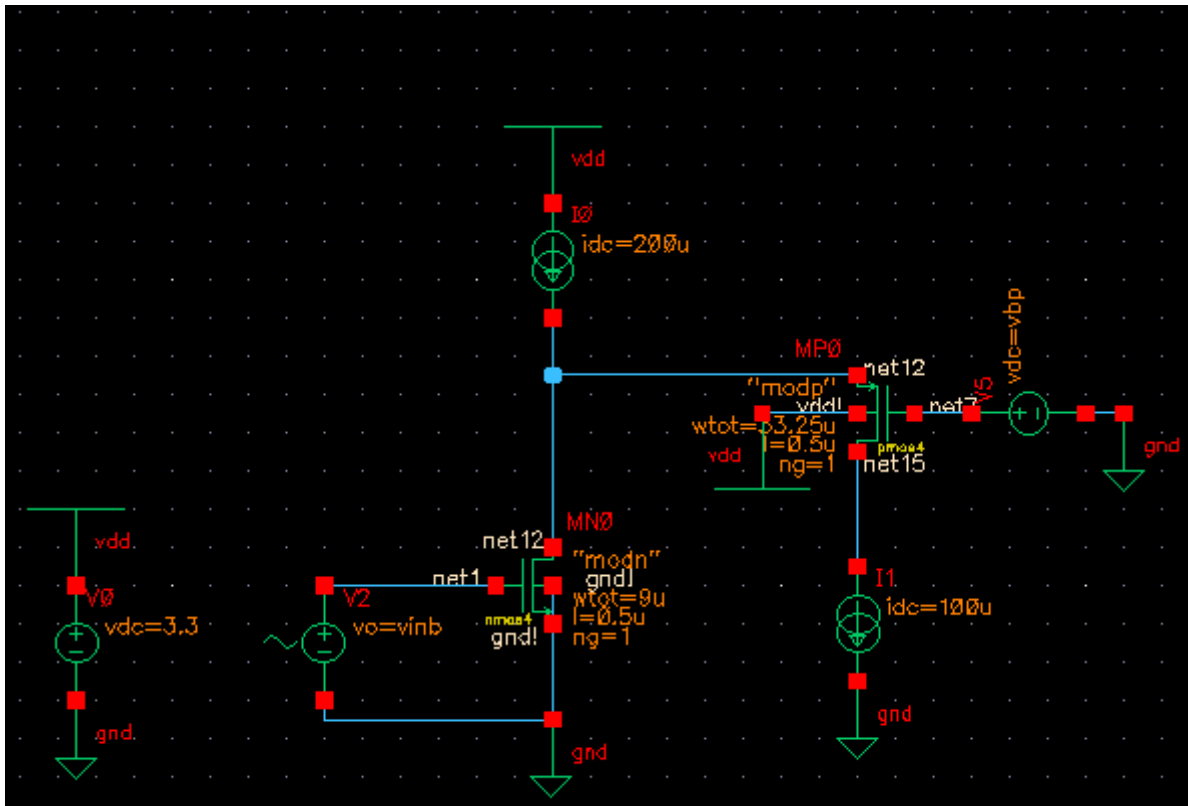


Figure 1.1: The Basic Schematic of Folded Cascode

In this assignment we are supposed to design a folded cascode, basically as shown in Fig.1.1, and possess following specifications:

**Gain:** around 70dB, **Output Impedance:** at least 2M ohm, **Unit Gain Freq:** 10MHz

The idea behind designing a folded cascode amplifier is to transform input voltage to a current and apply this current to common gate configuration. Therefore cascode structure combine large transconductance of CS amplifier and favorable frequency response of common gate stage. Thus, this configuration may offer higher gain, higher bandwidth and high input impedance.

As seen in Fig.1.1 we need additional constant current sources ( $I_0=200\mu\text{A}$  and  $I_1=100\mu\text{A}$ ) in order to bias nmos and pmos circuits with  $100\mu\text{A}$  currents. Also  $I_1$  behaves like an active load that is connected to drain of pmos common gate structure and output is taken on this active load. We need to implement these constant current sources by using current mirror configurations.

Designing process of Folded Cascode Amplifier can be divided into 2 stages:

- 1) Designing constant current sources and determining I-V characteristic of current mirrors.
- 2) Replacing constant currents sources in Fig.1.1 with current mirrors designed in first stage

and arranging operating points of transistors by changing aspect ratios (W/L) so that all mosfets operates in saturation region.

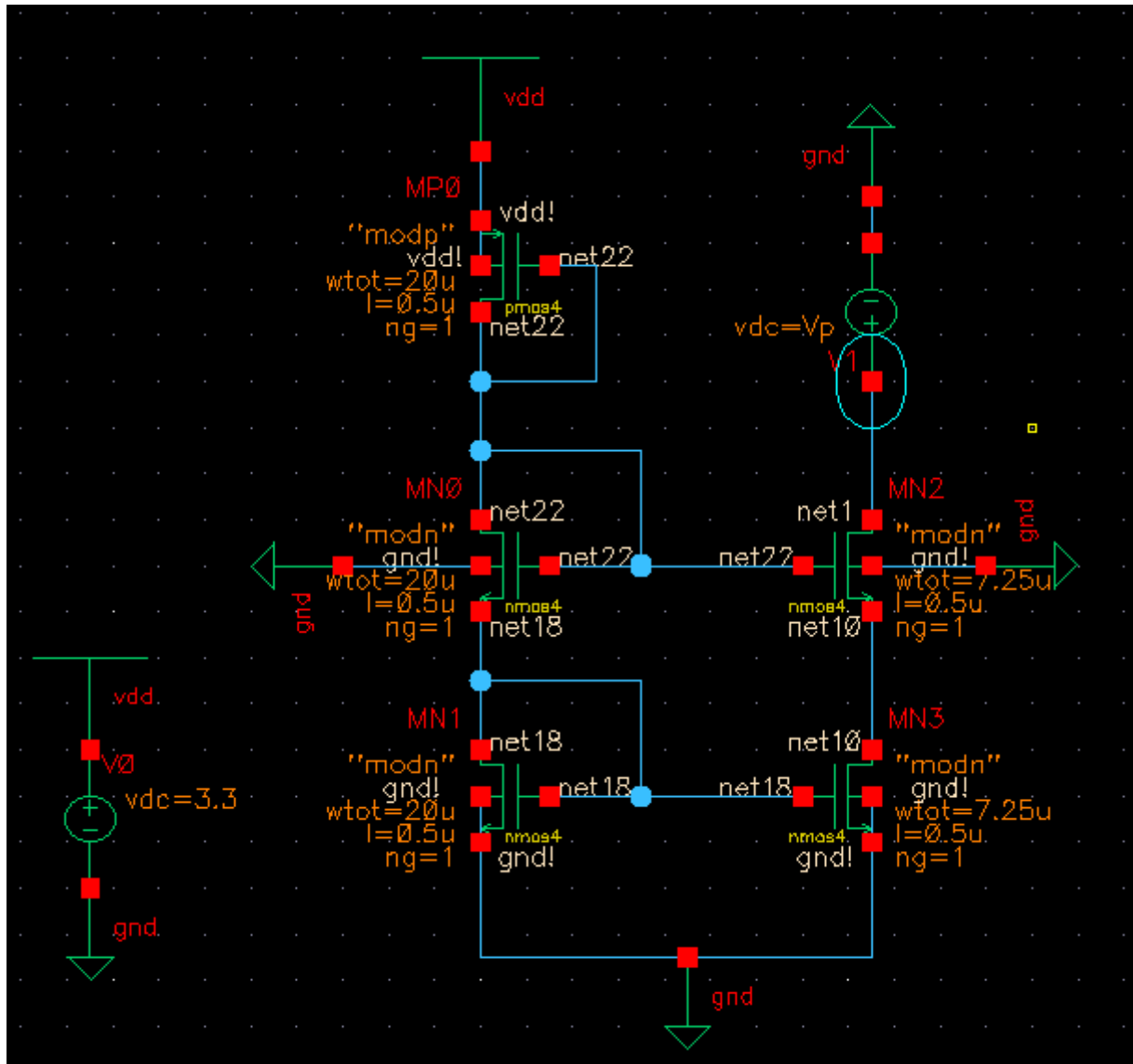


Figure 1.2: Implementing 100uA constant current source in Fig.1.1 by using Cascode MOS Mirror topology.

In order to implement 100uA current source (I1 in Fig.1.1), Cascode MOS Mirror structure is used rather than basic current mirror since cascoding increases output resistance of current source which behaves like as active load of folded cascode. The gain of folded cascode:

$$A_v = g_{m1} \cdot R_{out}, \text{ where } g_{m1} \text{ is the transconductance of nmos in Fig.1.1}$$

Thus by using a current mirror with high output resistance we can obtain higher gain around 70dB easily. Output Resistance of current mirror in Fig.1.2:

$$R_o = r_{o2} + [1 + (g_{m2} + g_{mb2})r_{o2}]r_{o3} \sim g_{m2} \cdot (r_o)^2$$

Also by using cascode current mirror it is easier to arrange stable currents in output while

operating basic current mirror structure is a bit challenging. Although we are favor of implementing cascode current mirror to benefit from its high output resistance, there is a drawback of this configuration like consuming large portion of VDD voltage and restricting our output voltage swing.

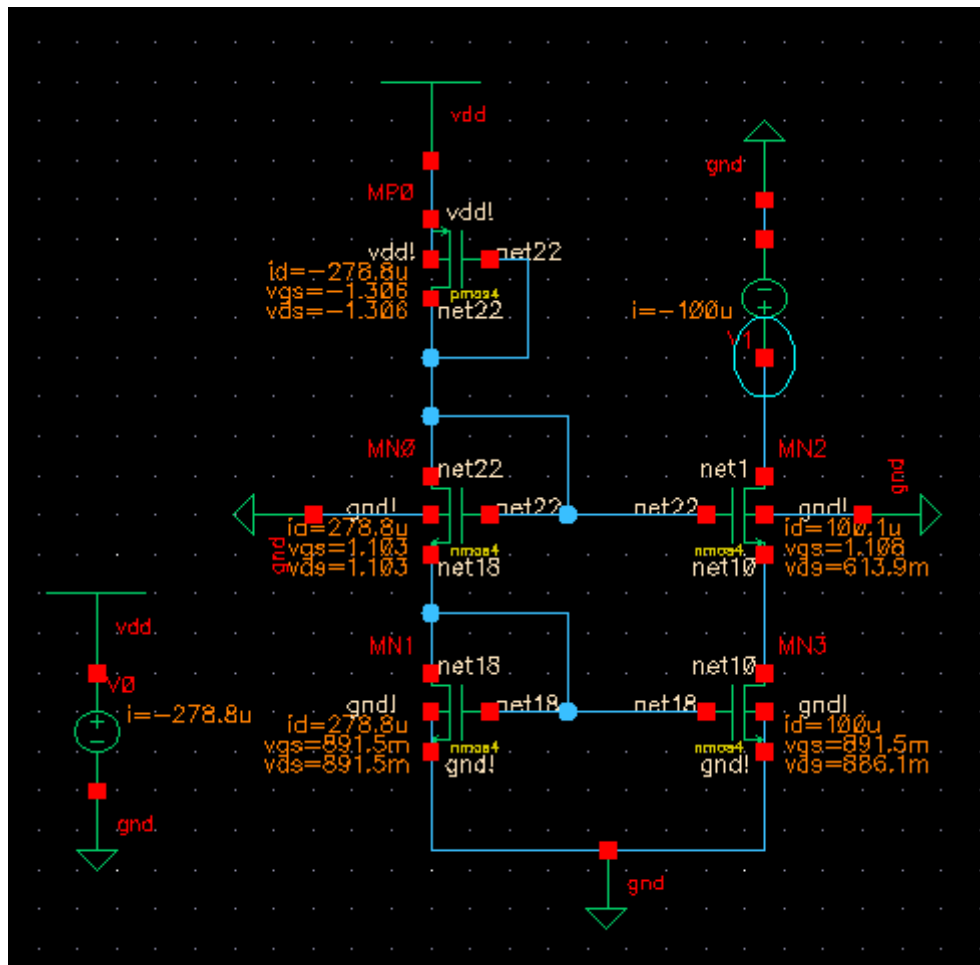


Figure 1.3: Quiescent Points of Cascode Current Mirror.

Generally  $V_{ov}$  values of MOS in the range of 0.2V-0.4V range so to be consistent with convention I assumed  $V_{ov}$  around 0.4V to make hand calculations. For  $I_D = 100\mu A$ ,  $V_{ov} = 0.4V$  for 0.5 $\mu m$  CMOS technology I deduced widths of MN2 and MN3 transistors approximately 3.3 $\mu m$ . Therefore I started to Cascode current mirror design by using this values for MN2 and MN3. However for this values I obtained  $V_{ov}$  voltages of MN2 and MN3 a bit higher than what I assumed. Probably this differences derived from the short channel effect. Then, in order to decrease overdrive voltages of MN2 and MN3, I tried different sets of values for transistors in Figure 1.2 and consequently I came up with values in Fig.1.2 and  $V_{ov} = 325mV$  for MN2 and MN3.

As seen in Fig.1.3 all transistors work in saturation region and we generate  $I_{ref} = 278.8\mu A$  current by simply using a diode connected pmos and we obtain 100 $\mu A$  as output current.

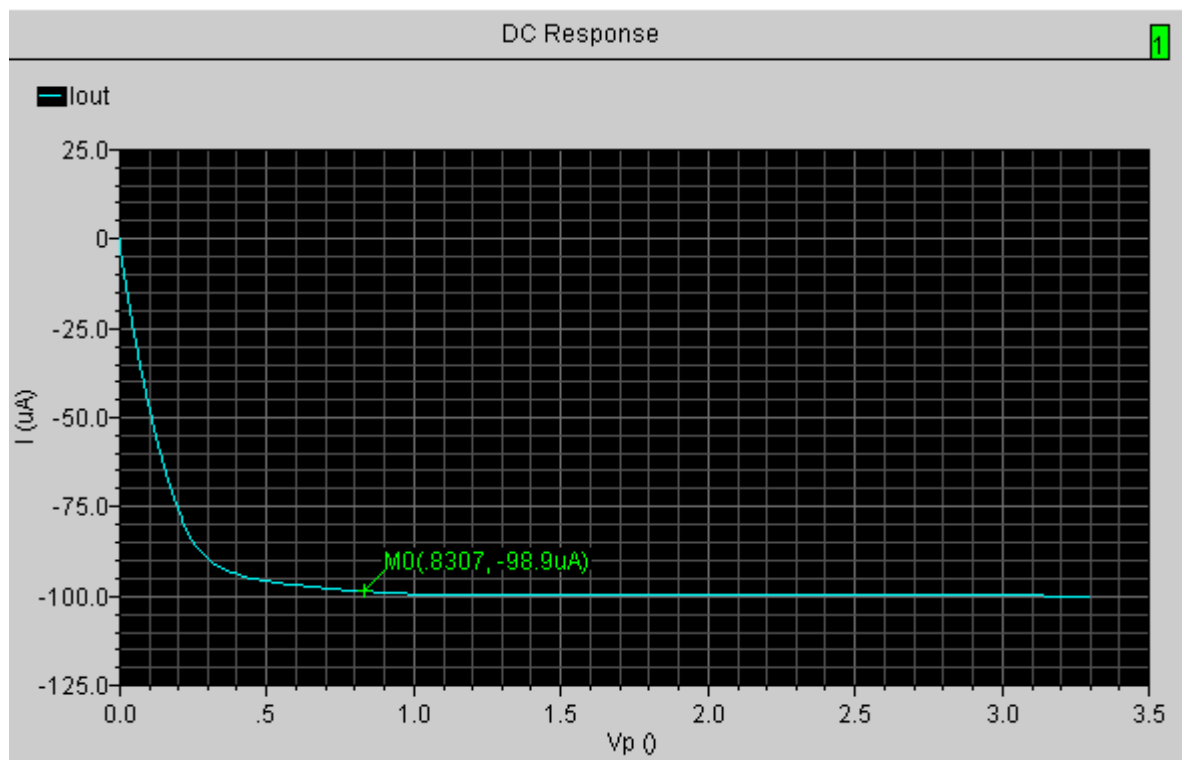


Figure 1.4:  $V_p$  vs  $I_{out}$  Graph of Cascode Current Mirror.

In Fig.1.4,  $I_{out}$  is not stable for  $0 < V_p < 0.8-0.9$  V whereas  $I_{out}$  can be considered as constant for  $V_p > 0.8-1$  V. The reason is that for  $0 < V_p < 0.8-0.9$  V MN2 and MN3 nmos transistors are not in the saturation region simultaneously and for  $V_p > 0.8-0.9$  V all transistors operates in saturation region. Also we can interpret Figure 1.4 as that, in order to implement circuit in Fig 1.2 as a 100 $\mu A$  constant current source in folded cascode configuration of Fig.1.1, we need to bias  $V_p$  in the range roughly 1V to 3.3V

Another observation about this current mirror is that it pull current and functions like a current sink.



drain of MP8. The results roughly was that : for  $0 < V_{DP8}(\text{voltage at drain of MP8}) < 2.3V$

200uA constant current is obtained and for  $V_{DP8} > 2.3V$  current through MP8 and MP6 starts to decay since these two transistors are not in saturation region simultaneously.

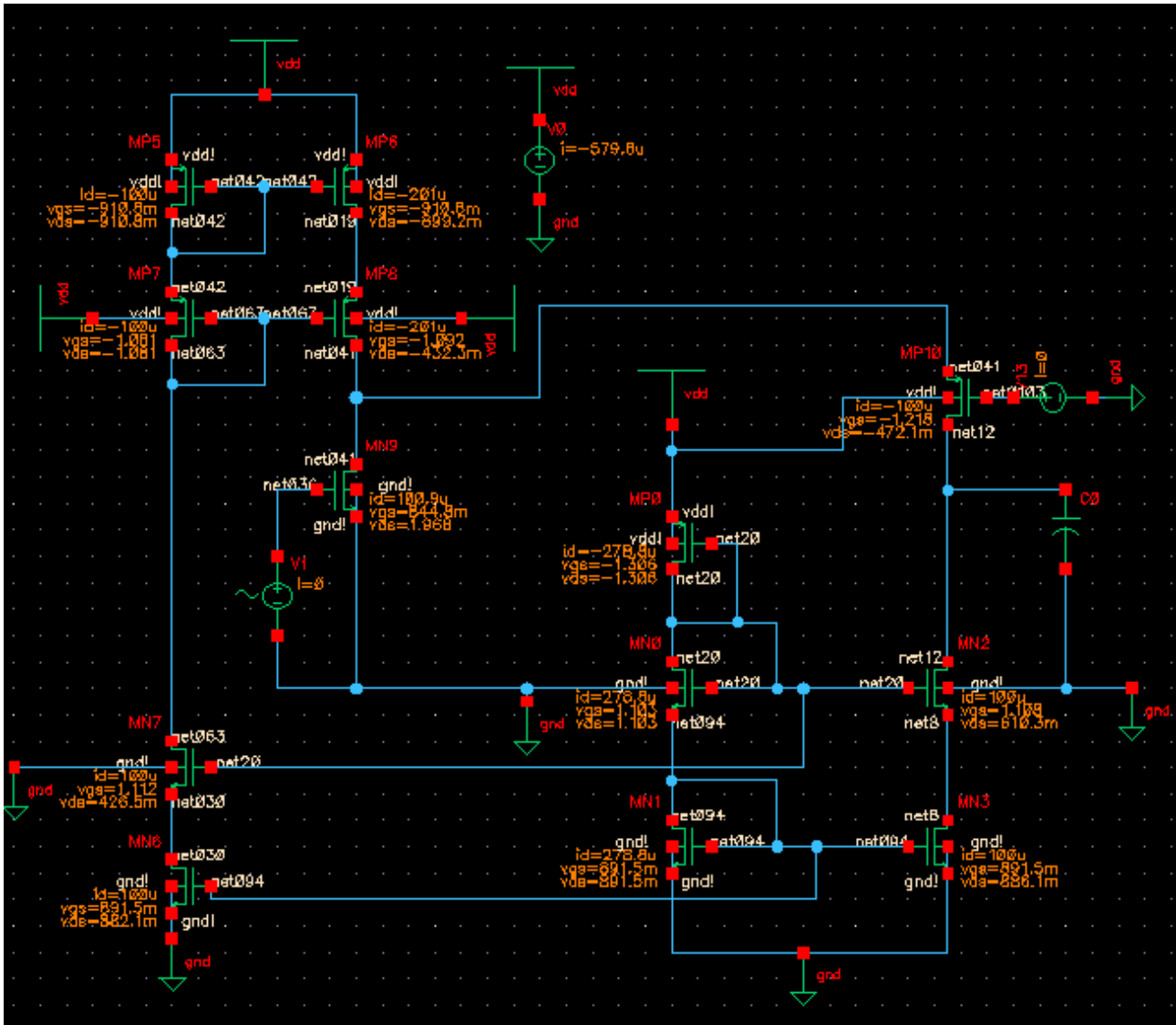


Figure 1.6: DC Operating Points of Folded Cascode Design.

As seen in Fig.1.6 all mosfets that are used in designing process of Folded Cascode Amplifier are biased in saturation region. In order to accomplish this,  $V_{inb} = 0.8448V$  offset voltage is given in input terminal and  $V_{bias} = 0.75V$  is given to gate of MP10. The reason for choosing  $V_{inb} = 0.8448$  is that when we sweep a dc input voltage and plot  $V_o/V_i$  transfer characteristic of circuit,  $V_{inb} = 0.8448$  was the point that slope is steepest or in other words  $A_v = V_o/V_i$  is highest.

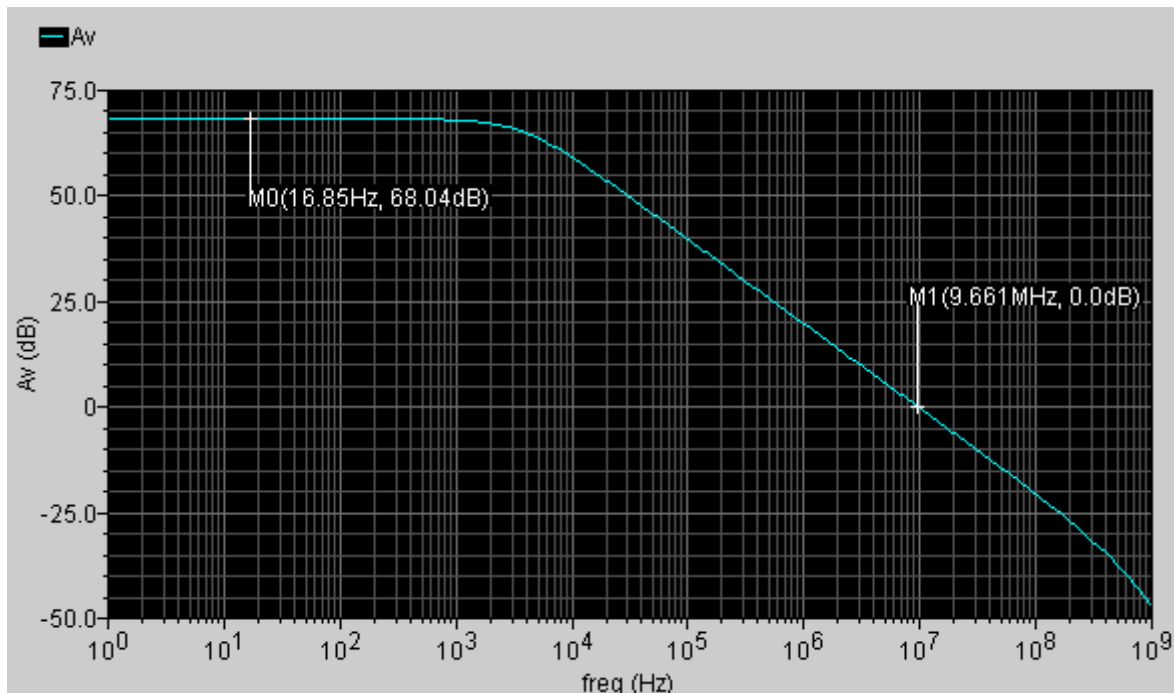


Figure 1.7: Gain-Frequency graph of Folded Cascode.

As seen in graph above, unity gain frequency is  $f_u = 9.661\text{MHz}$  and  $A_v = 68\text{dB}$  for low frequencies. In order to obtain higher gain (like above 70dB) I can increase  $L$  of MN2 and MN3. The idea behind increasing  $L$  is that  $\lambda$  is inversely proportional to the length selected for channel. Thus increasing  $L$  leads to decreasing of  $\lambda$  and we obtain larger  $r_o$  values for MN2 and MN3 since  $r_o = 1/(\lambda I_D)$ . As it is stated before active load implemented by 100uA current mirror is roughly  $g_{m2} \cdot (r_o)^2$  and increasing of  $L$  lead to larger  $R_{out}$  and in return it triggers higher gain.

Deducing  $R_{out}$ :

$$A_v = g_m \cdot R_{out} \text{ where } g_m \text{ is transconductance of MN9}$$

$$A_v = 68\text{dB} \sim 2500\text{V/V}$$

$$g_m = 616.6\mu\text{A/V (obtained by checking parameters of MN9)}$$

$$R_{out} = A_v / g_m = 2500 / 616.6 \sim 4\text{M ohm}$$

Also we could check  $R_{out}$  by applying a small test voltage  $v_x$ , and finding current  $i_x$  drawn from  $v_x$ .

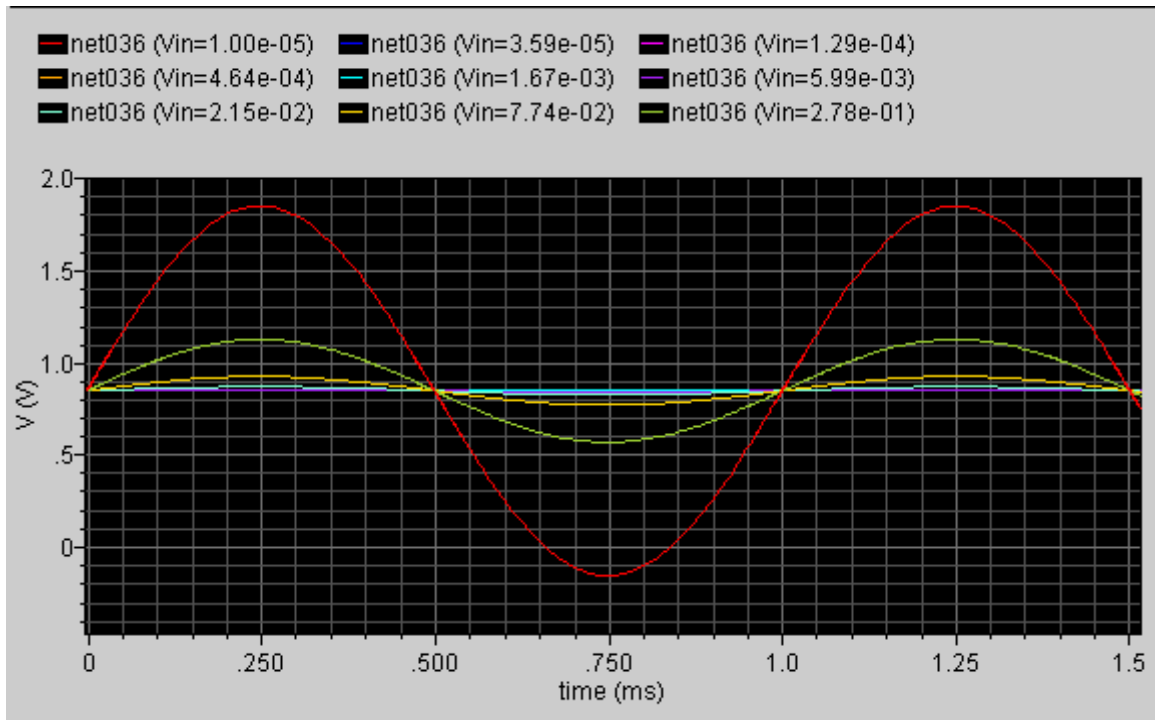


Figure 1.8: Input Voltage Swing

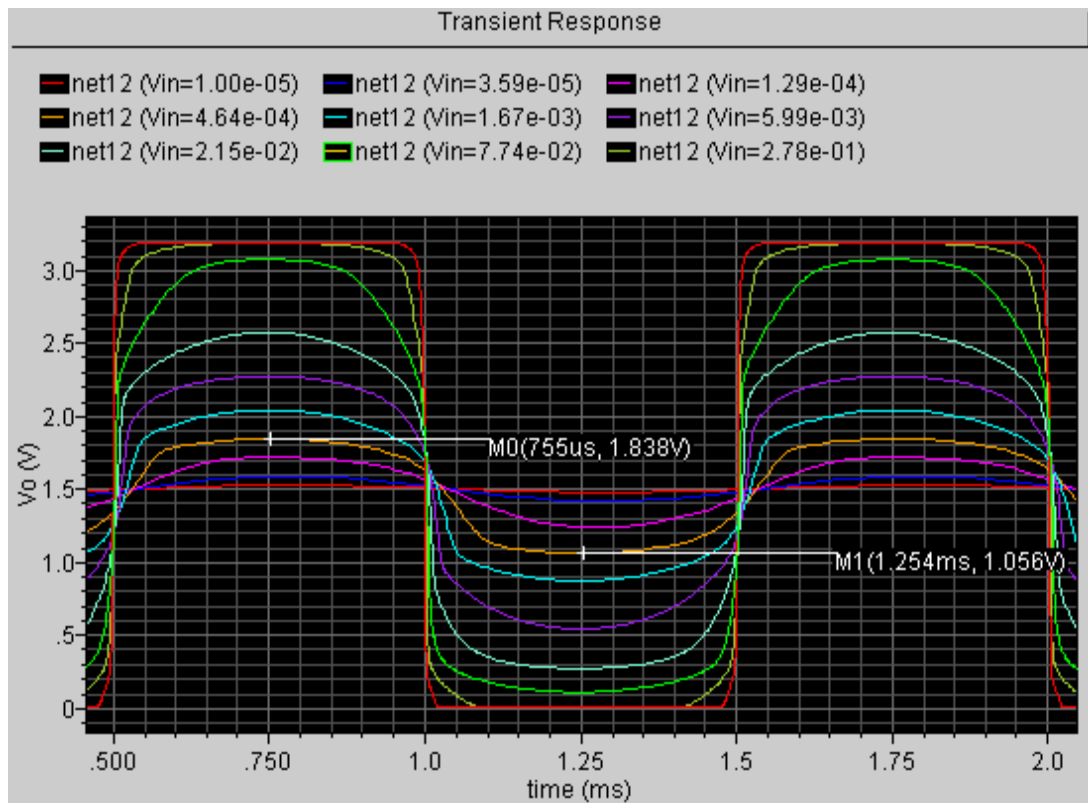


Figure 1.9: Output voltage swing corresponding to input voltage in Fig.1.8 analysis.

As seen in Fig.1.9, output voltage start to distort and clip around  $v_{omax}=1.83V$  and  $v_{omin}=1V$ . Therefore it can be said that voltage swing is from 1V to 1.838V. This is also coincide with expectations since output voltage is restricted from below (across 100uA current source) roughly by  $V_{th}+2V_{dsat}\sim 1.1V$ . In addition output voltage headroom is restricted by 3pmos (MP6,

MP8, MP10) so that  $v_{omax} \sim 3.3V - 3V_{ov} \sim 2.1V$ .

BONUS 1:

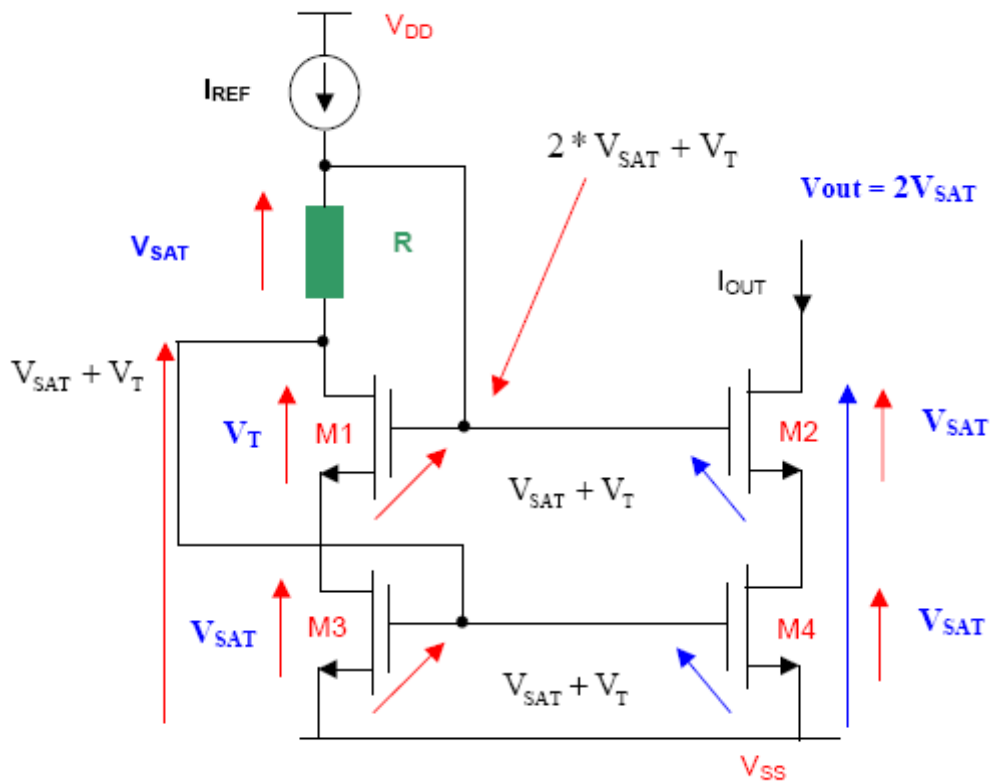


Figure 1.10: Modified Cascode Current Sink to reduce voltage drop across M2 and M4 and increase output voltage swing.

Although voltage drop across M2 and M4 is  $2V_{sat} + V_t$  for Cascode Current Mirror that we used in Folded Cascode design, modified current sink configuration shown as in Fig.1.10, offers a voltage drop  $2V_{sat}$ . Thus  $v_{omin}$  is decreased by a amount  $V_t \sim 0.7V$  and voltage swing is improved by same amount.

Rout	Av	Unity Gain Freq.	Output Swing
~4M ohm	68dB	9.661MHz	1.05V to 1.83V

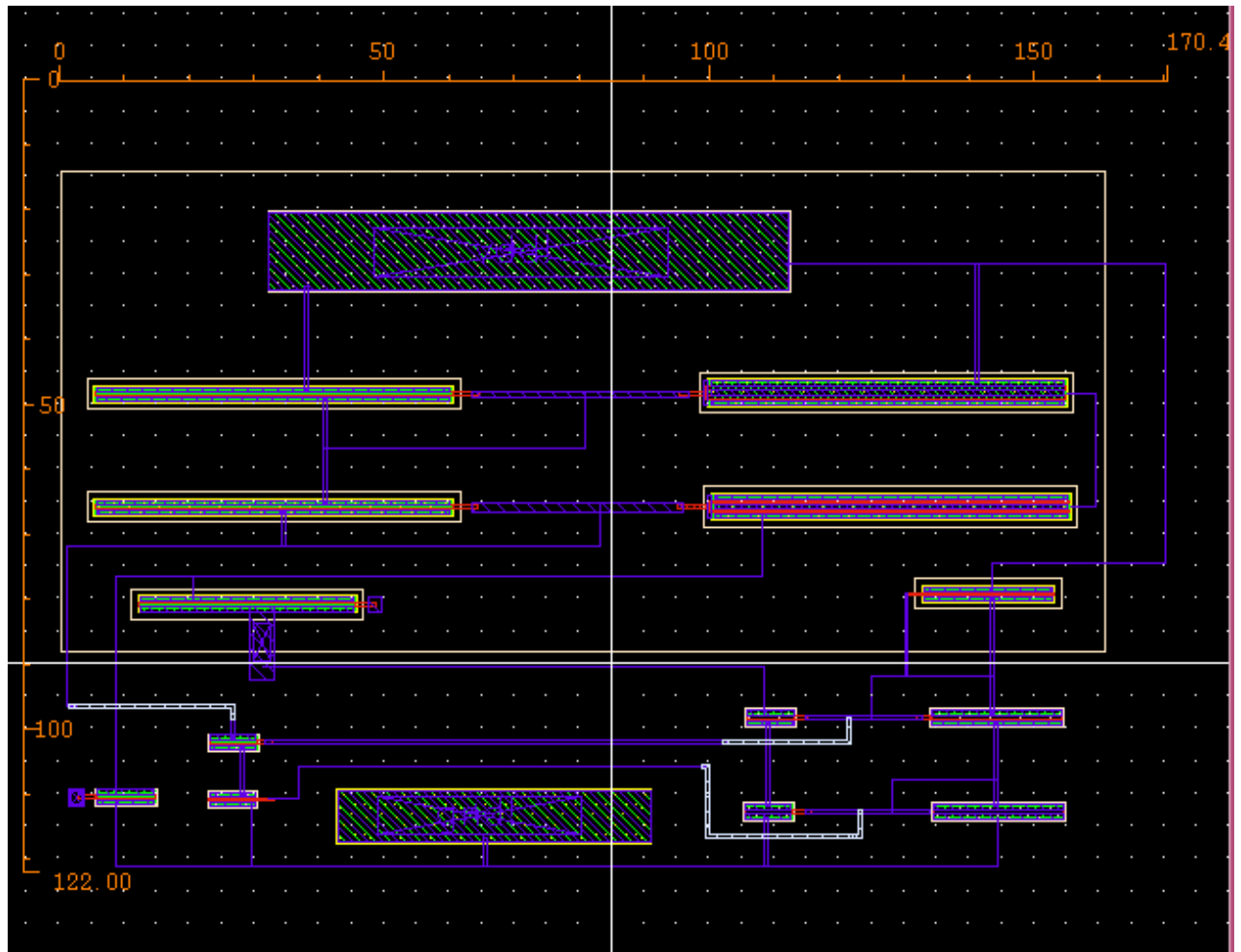


Figure 1.1: General Outlook of Folded Cascode Layout

Layout of the folded cascode amplifier that is designed in schematic level as previous assignment can be seen in *Fig.1.1* . As seen in figure, layout design covers an area approximately  $122 \times 10^{-6} \times 170 \times 10^{-6} \cong 0.02 \times 10^{-6}$  . This value for folded cascade layout's area is quite high and it can be decreased by further compression such as increasing number of gates of transistors that possess large width (for pmos transistors that have 110um and 55um widths), bringing mosfets closer to each other and using minimum available paths for metal connections.

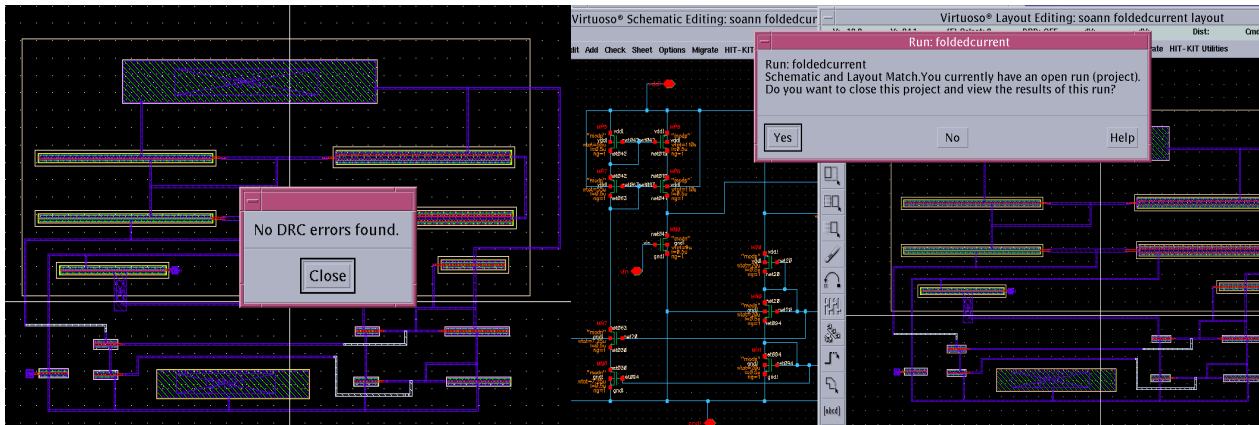


Figure 1.2: DRC and LVS analysis of folded cascade layout.

As seen in Figure 1.2, no DRC errors found (for grid, no antenna, no coverage, no erc and no generated layers) and layout and schematic of folded cascade amplifier is matched.

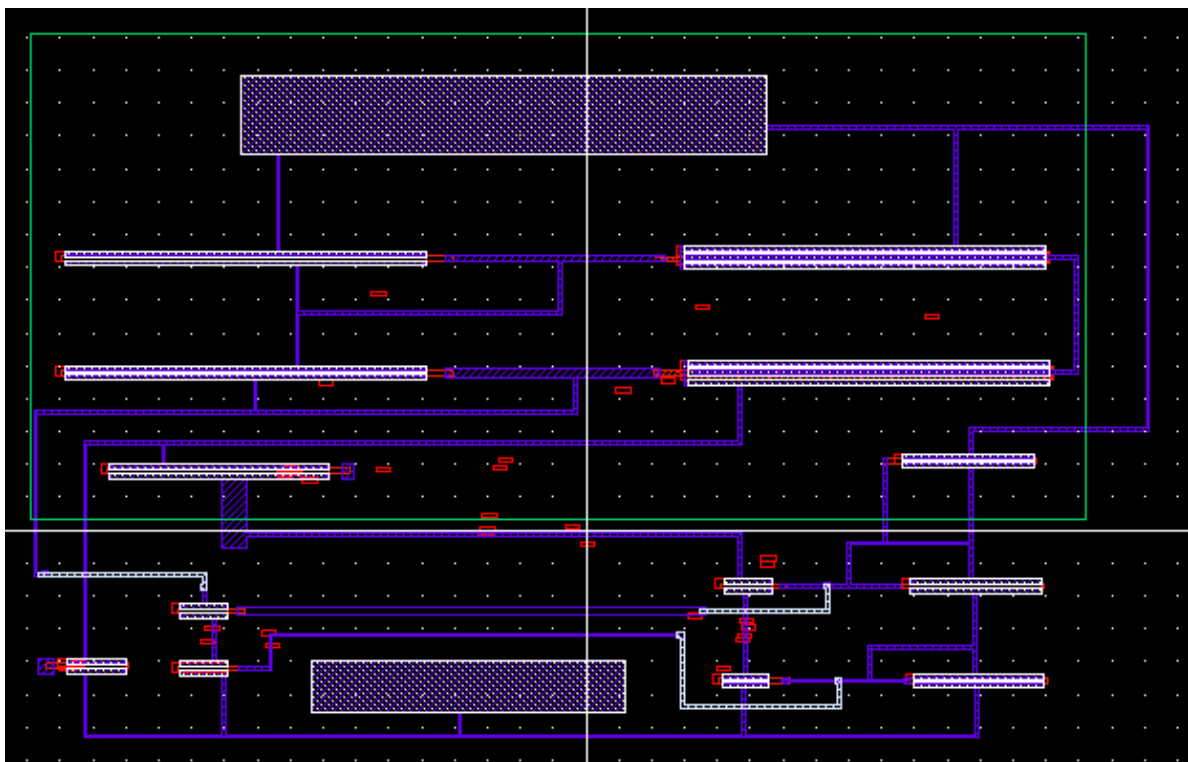


Figure 1.3: Layout of Folded Cascade with Parasitic Capacitances.

When RCX analysis of layout for only C is done, as seen in *Fig. 1.2*, layout contains lots of small parasitic capacitances that derives from interconnects and source/drain areas, affects performance of circuit by changing dc operating points of transistors and frequency response of circuit. Prominent of these capacitances (larger ones) are listed in *Table 1*.

C Values	30.14fF	20.48fF	17.16fF	11.63fF	9.474fF
C Values	8.313fF	6.675fF	5.354fF	4.717fF	4.577fF

Table 1: Values of high capacitances encountered in Fig.1.3.

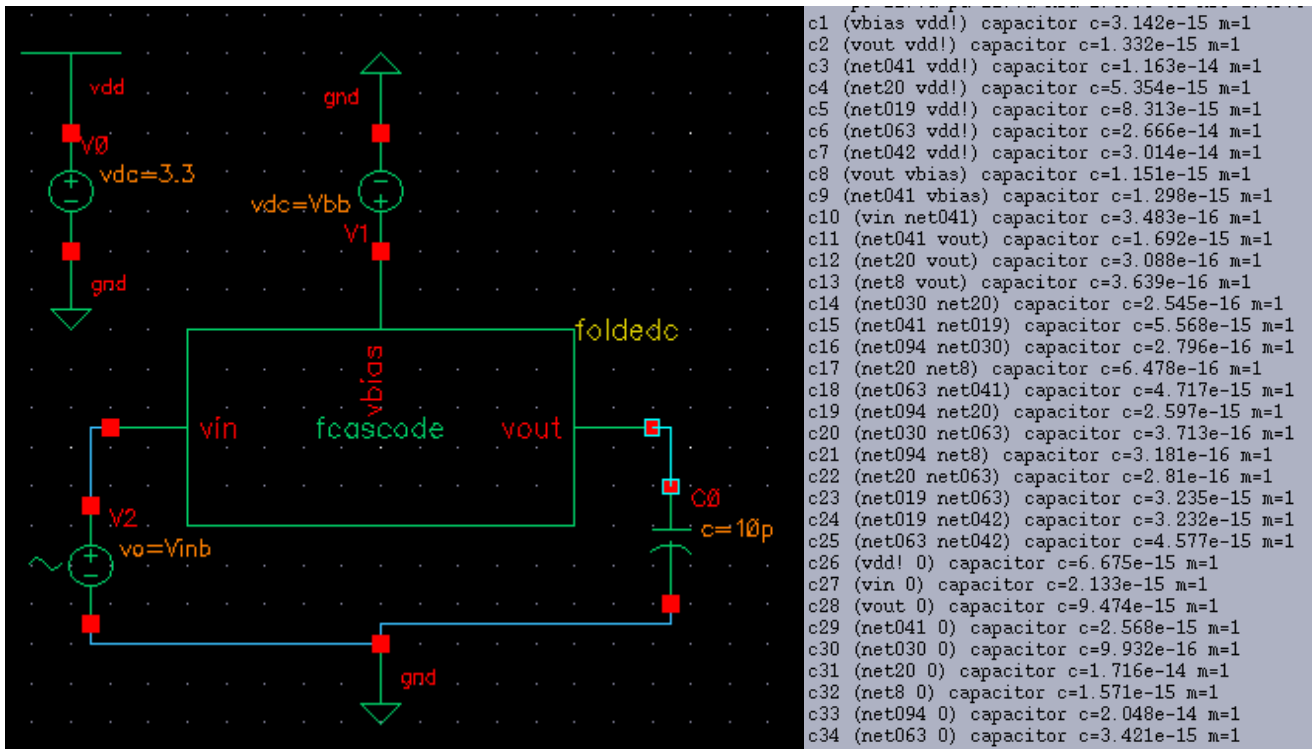


Figure 1.4: Schematic of Post-Layout Simulation and Capacitances in Netlist.

As stated before, how the layout is designed is crucial in effecting the performance of circuit since parasitic capacitances are generated according to it. In order to determine how the folded cascode would work from layout we need to perform a post-layout simulation by using the schematic shown in *Fig. 1.4*. As seen in netlist, there are 34 capacitances extracted from layout (match with Table 1 too) and we will take into account all these parasitic capacitances while doing simulation.

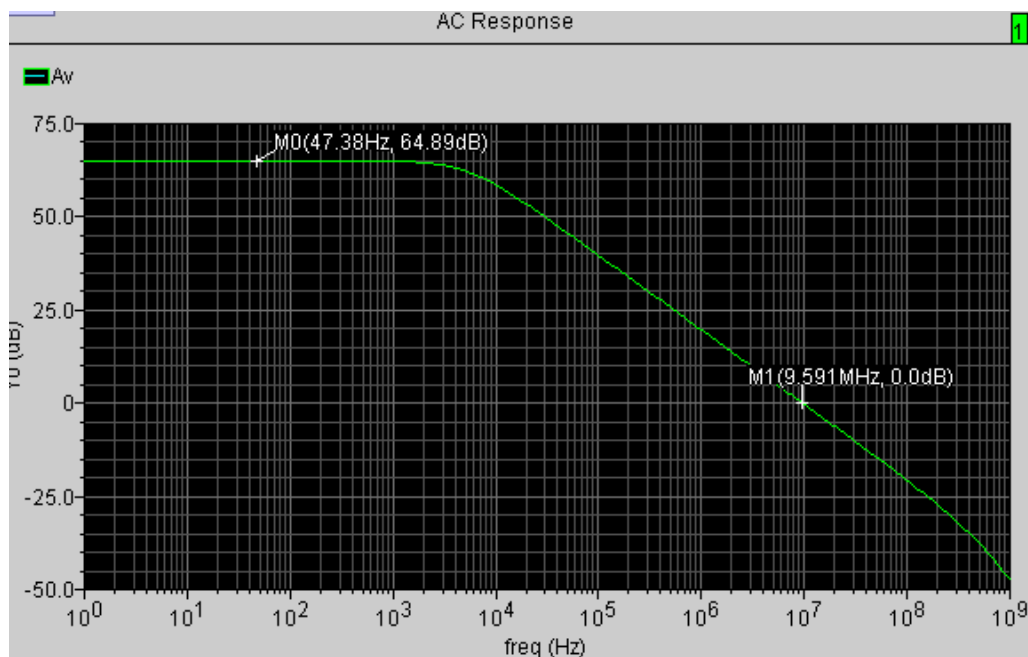


Figure 1.5: Gain-Frequency graph of Folded Cascode with parasitic capacitances for  $V_{inb}=844.8\text{mV}$  and  $V_{bb}=481.5\text{mV}$ .

As stated in previous lab report, we had biased circuit in schematic level with 0.8448V offset voltage in input and  $V_{bb}=0.75V$  in the gate of pmos whose drain is used to take output. When these values are entered as post-layout schematic bias voltages, transistor marked in Figure 1.6 operates in triode region and thus gain decreases to roughly  $A_v = 40dB$ .

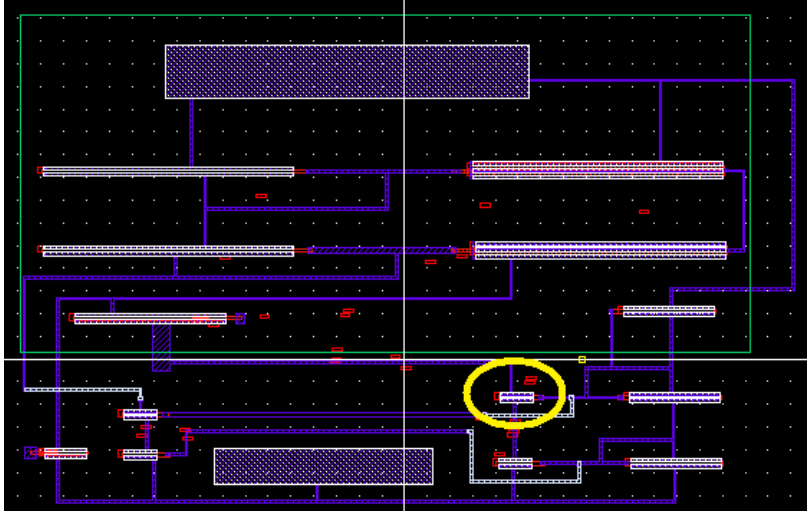


Figure 1.6: Marked NMOS transistor of constant current source operates in triode region for  $V_{bb}=0.75V$  and  $V_{inb}=0.8448$  for circuit in Fig.1.4.

Constant current source behave like active load of folded cascode ( $R_o \cong gm \cdot r_o^2$ ) where  $g_m$  and  $r_o$  belong to marked nmos and nmos below it. Thus while marked transistor is in triode, output resistance of it decreases and active load of folded cascode ( $R_o$ ) decreases. This is the reason of decrease in gain.

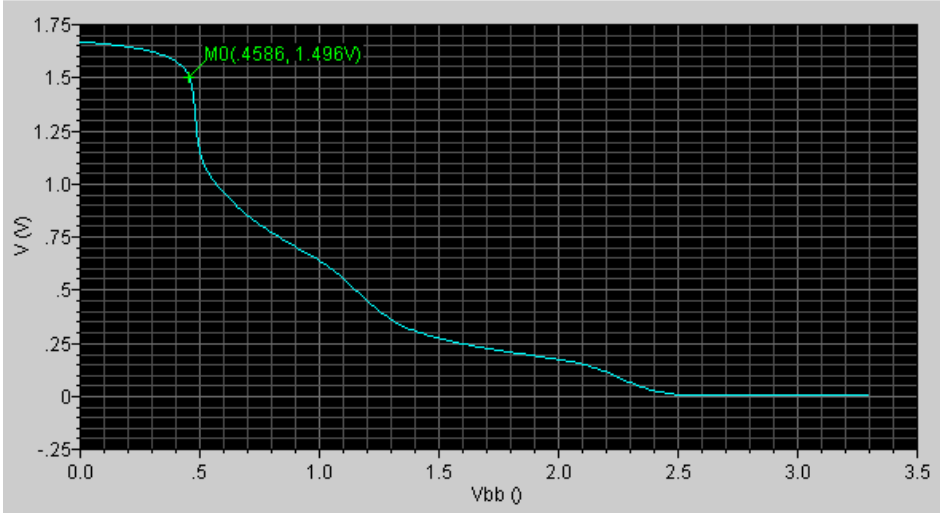


Figure 1.7: Sweep Analysis of  $V_{bb}$  bias voltage. It is obvious from graph for  $V_{bb}=0.75V$ ,  $V_o$  biased around 0.8V and thus constant current source does not perform properly.

As we recall from report of schematic design, constant current source for  $I=100\mu A$  was working properly for  $V_o$  biased at roughly in the range 1V to 3.3V and we had biased folded cascode for  $V_o = 1.496V$ . Therefore, in order to determine whether it is possible to bias  $V_o$  around 1.496V while parasitic capacitances are considered, sweep analysis



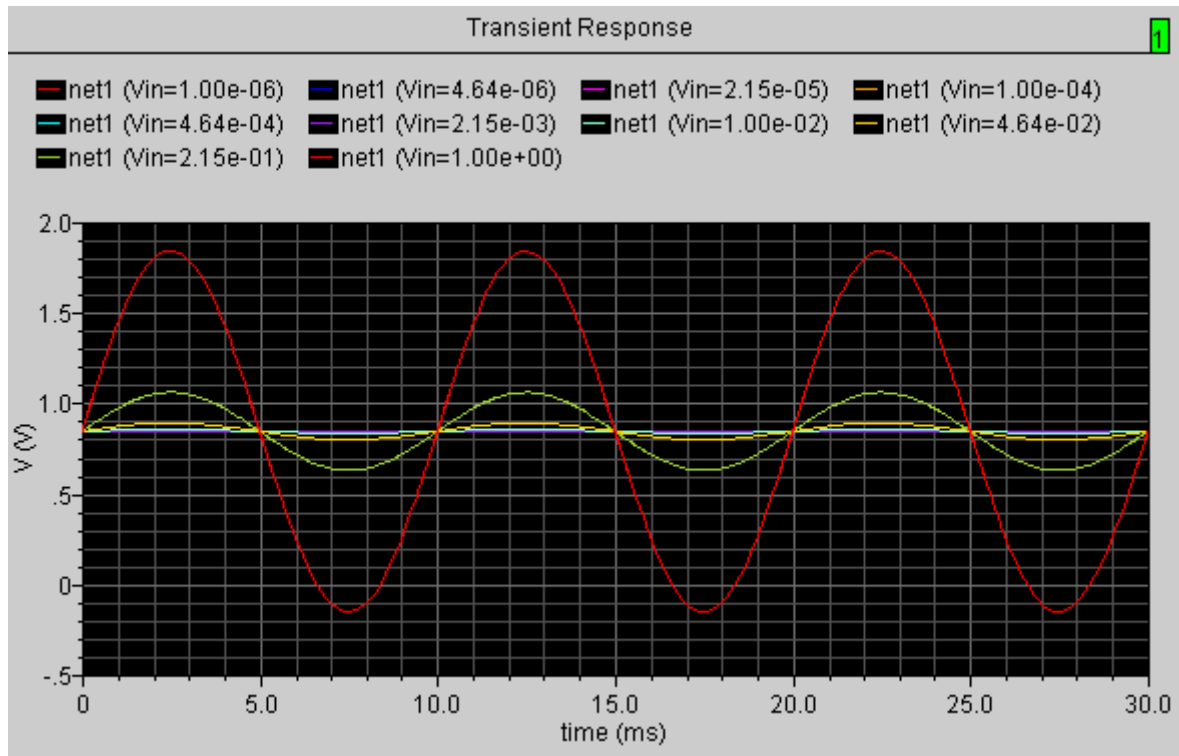


Figure 1.9: Input voltage swing.

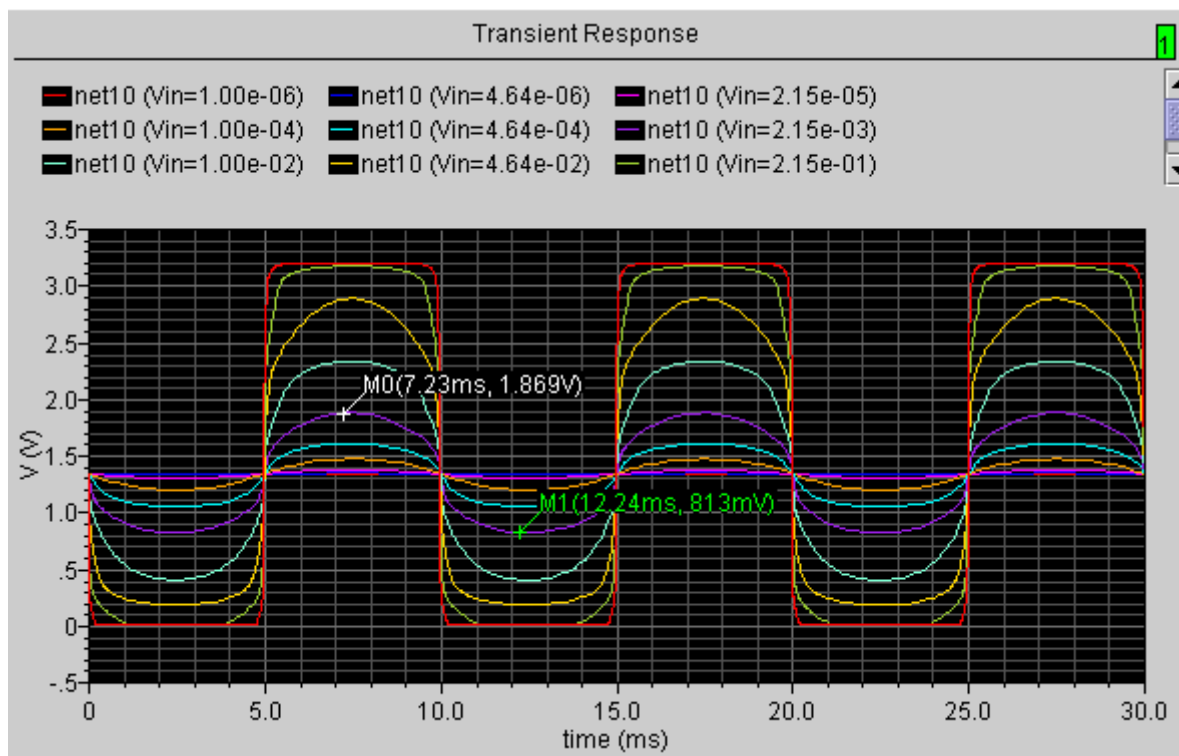


Figure 1.10: Output voltage swing corresponding to input voltage in Fig 1.9

As seen in Fig.1.10, output voltage start to distort and clip around  $v_{omax} = 1.869V$  and  $v_{omin} = 0.813V$ . Thus output voltage swing is from 0.813V to 1.869V.

	Av	Rout	Unity Gain Frequency	Output Swing
Schematic	68dB	4Mohm	9.661MHz	1.05V to 1.83V
Layout	64.89dB	2.87Mohm	9.591Mhz	0.813V to 1.869
Deviation	%4.5	%28.25	%0.72	%2

Table 2: Comparison of values obtained in schematic and layout simulation with extracted capacitances.